

## NPN 2A 60V Middle Power Transistor

Parameter	Value		
$V_{CEO}$	60V		
I <sub>C</sub>	2A		

#### Features

1) Suitable for Middle Power Driver

2) Complementary PNP Types: 2SA2094

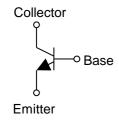
3) Low V<sub>CE(sat)</sub>

 $V_{CE(sat)}$ =0.50V(Max.)

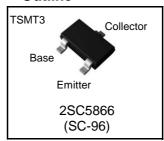
 $(I_C/I_B = 1A / 0.1A)$ 

4) Lead Free/RoHS Compliant.

## •Inner circuit



#### Outline



## Applications

Motor driver , LED driver Power supply

## Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SC5866	TSMT3	2928	TL	180	8	3,000	VL

## ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Values	Unit
Collector-base voltage		V <sub>CBO</sub>	60	V
Collector-emitter voltage		V <sub>CEO</sub>	60	V
Emitter-base voltage		$V_{EBO}$	6	V
Collector current	DC	I <sub>C</sub>	2.0	А
	Pulsed	I <sub>CP</sub> *1	4.0	А
Power dissipation		P <sub>D</sub> *2	0.5	W
Junction temperature		T <sub>j</sub>	150	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +150	°C

<sup>\*1</sup> Pw=10ms, single pulse

<sup>\*2</sup> Each terminal mounted on a reference land

## ●Electrical characteristics (Ta = 25°C)

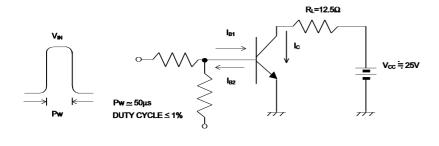
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	60	-	-	V
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 100μA	60	-	-	V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> = 100μA	6	ı	ı	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40V	ı	ı	1.0	μА
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	1	-	1.0	μА
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *1	$I_C = 500 \text{mA}, I_B = 25 \text{mA}$	-	200	500	mV
DC current gain	h <sub>FE</sub>	$V_{CE} = 2V, I_{C} = 100mA$	120	-	390	-
Transition frequency	f <sub>T</sub> *1	$V_{CE} = 10V, I_{E} = -100 \text{mA}$ f=10MH <sub>Z</sub>	-	200	-	MHz
Output capacitance	C <sub>ob</sub>	$V_{CB} = 10V$ , $I_E = 0A$ f = 1MHz	-	10	-	pF
Turn-on time	t <sub>on</sub> *2	I <sub>C</sub> =2A	-	50	-	ns
Storage time	t <sub>stg</sub> *2	I <sub>B1</sub> =200mA I <sub>B2</sub> = -200mA	-	120	-	ns
Fall time	t <sub>f</sub> *2	V <sub>cc</sub> ≃25V	-	35	-	ns

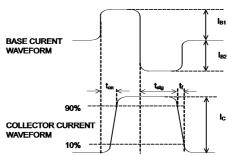
<sup>\*1</sup> Pulsed

# ●h<sub>FE</sub> rank categories

Rank	Q	R
h <sub>FE</sub>	120 to 270	180 to 390

# •Switching time test circuit





<sup>\*2</sup> See switching time test circuit

## ●Electrical characteristic curves(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

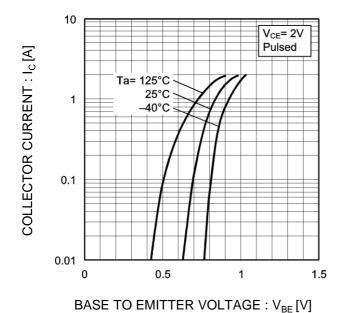
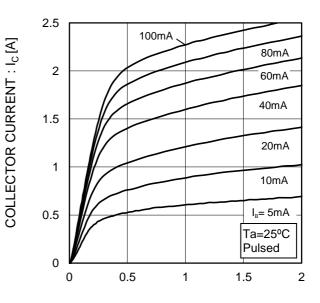


Fig.2 Typical Output Characteristics



COLECTOR TO EMITTE VOLTAGE :  $V_{CE}[V]$ 

Fig.3 DC Current Gain vs. Collector Current (I)

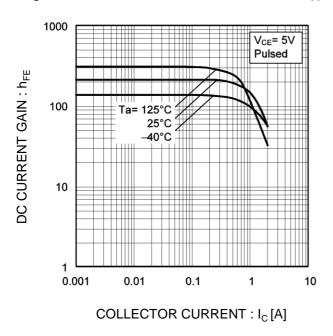
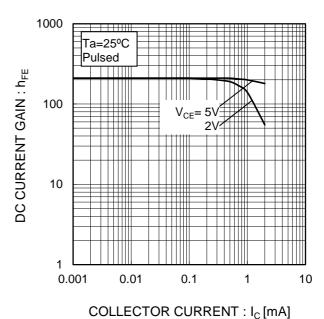


Fig.4 DC Current Gain vs. Collector Current (II)



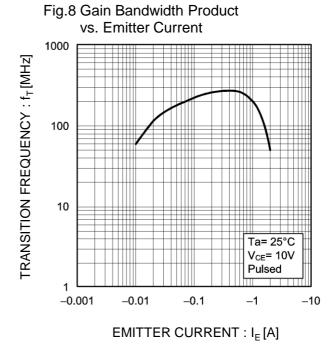
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### ●Electrical characteristic curves(Ta = 25°C)

Fig.5 Collector-Emitter Saturation Voltage

vs. Collector Current (I) 10  $I_{\rm C}/I_{\rm B}=10/1$ COLLECTOR-EMITTER SATURATION VOLTAGE : V<sub>CE(sat)</sub> [V] Pulsed 1 Ta= 125°C 25°C 0.1 0.01 0.001 0.01 0.1 1 10 COLLECTOR CURRENT : I<sub>C</sub>[A]

Fig.7 Base-Emitter Saturation Voltage vs. Collector Current 10  $I_{\rm C}/I_{\rm B}=10/1$ BASE-EMITTER SATURATION VOLTAGE : V<sub>BE(sat)</sub> [V] Pulsed Ta= -40°C 25°C 125°C 0.1 0.01 0.001 0.01 0.1 1 10 COLLECTOR CURRENT: Ic [A]



## ●Electrical characteristic curves(Ta = 25°C)

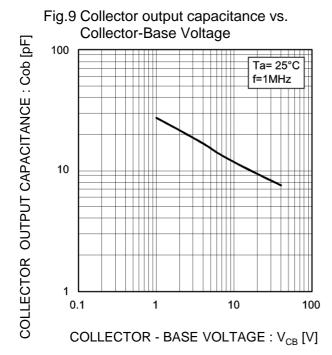
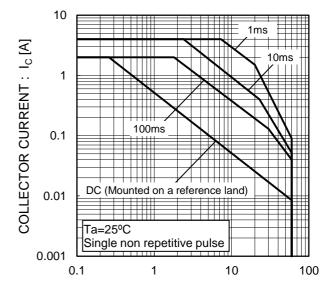


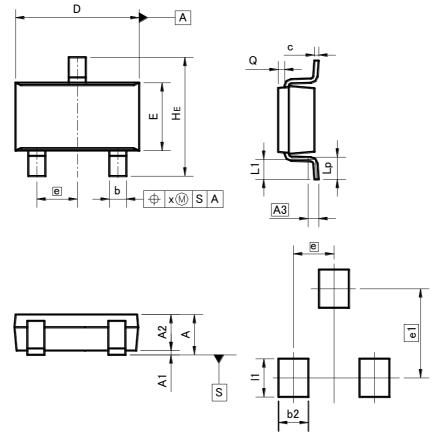
Fig.10 Safe Operating Area



COLLECTOR TO EMITTER VOLTAGE :  $V_{CE}\left[V\right]$ 

## ●Dimensions (Unit : mm)

## TSMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	ı	1.00	_	0.039	
A1	0.00	0.10	0.000	0.004	
A2	0.75	0.95	0.030	0.037	
A3	0.3	25	0.0	10	
b	0.35	0.50	0.014	0.020	
С	0.10	0.26	0.004	0.010	
D	2.80	3.00	0.110	0.118	
E	1.50	1.80	0.059	0.071	
е	0.95		0.037		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.05	0.25	0.002	0.010	
Х	_	0.20	_	0.008	

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b2		0.70	_	0.028	
e1	2.10		0.0	83	
l1	ı	0.90	ı	0.035	

Dimension in mm / inches

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